

Form PTO-1449	U.S. Department of Commerce Patent and Trademark Office	Attorney Docket No. 5308-162	Serial No. To Be Assigned
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)		Applicants: Robert C. Glass et al.	
		Filing Date: To Be Assigned	GAU:

## U.S. PATENT DOCUMENTS

Examiner Initials		Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate
	1	6,177,688	01/23/01	Linthicum et al.	257	77	
	2	6,169,294	01/02/01	Biing-Jye et al.	257	79	
	3	6,133,589	10/17/00	Krames et al.	257	103	
	4	6,121,637	09/19/00	Isokawa et al.	257	99	
	5	6,121,636	09/19/00	Morita et al.	257	99	
	6	6,097,041	08/01/00	Lin et al.	257	98	
	7	6,091,085	07/18/00	Lester	257	98	
	8	6,046,465	04/04/00	Wang et al.	257	98	
	9	5,952,681	09/14/99	Chen	257	89	
	10	5,917,202	06/29/99	Haitz et al.	257	98	
	11	5,912,477	06/15/99	Negley	257	95	
	12	5,779,924	07/14/98	Krames et al.	216	24	
	13	5,767,581	06/16/98	Nakamura et al.	257	749	
	14	5,718,760	02/17/98	Carter et al.	117	84	
	15	5,523,589	06/04/96	Edmond et al.	257	77	
	16	5,416,342	05/16/95	Edmond et al.	257	76	
	17	5,393,993	02/28/95	Edmond et al.	257	77	
	18	5,247,533	09/21/93	Okazaki et al.	372	45	
	19	5,210,051	05/11/93	Carter, Jr.	437	107	
	20	5,187,547	02/16/93	Niina et al.	257	77	
	21	5,087,949	02/11/92	Haitz	357	17	
	22	5,006,908	04/09/91	Matsuoka et al.	357	17	
	23	4,966,862	10/30/90	Edmond	437	100	

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		Document Number	Date	Country	Class	Subclass	Translation Yes / No
	24	GB 2 346 480 A	08/09/00	United Kingdom			
	25	2000-195827	07/14/00	Japan			X (Abstract)
	26	EP 0 961 328 A2	12/01/99	EPO			
	27	10-256604	09/25/98	Japan			X (Abstract)
	28	9-82587	03/28/97	Japan			X (Abstract)
	29	1-225377	09/08/89	Japan			X (Abstract)
	30	56-131977	10/15/81	Japan			X (Abstract)

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	31	OSRAM Enhances Brightness of Blue InGaN LEDs, Compound Semiconductor, Volume 7, No. 1, February 2001, p. 7
	32	Craford, Outlook for AllInGaP Technology, Presentation, Strategies in Light 2000
	33	Krames et al., High-Power Truncated-Inverted-Pyramid (Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>0.5</sub> In <sub>0.5</sub> P/GaP Light-Emitting Diodes Exhibiting >50% External Quantum Efficiency, Applied Physics Letters, Vol. 75, No. 16, October 18, 1999, pp. 2365-2367
	34	Lambrech et al., Band Structure Interpretation of the Optical Transitions Between Low-Lying Conduction Bands in n-Type Doped SiC Polytypes, Materials Science Forum, Vols. 264-268, 1998, pp. 271-274
	35	Craford, Overview of Device Issues in High-Brightness Light-Emitting Diodes, Chapter 2, High Brightness Light Emitting Diodes: Semiconductors and Semimetals, Vol. 48, Stringfellow et al. ed., Academic Press, 1997, pp. 47-63
	36	Yoo et al., Bulk Crystal Growth of 6H-SiC on Polytype-Controlled Substrates Through Vapor Phase and Characterization, Journal of Crystal Growth, Vol. 115, Vol. 1991, pp. 733-739
	37	Biederman, The Optical Absorption Bands and Their Anisotropy in the Various Modifications of SiC, Solid State Communications, Vol. 3, 1965, pp. 343-346
	38	U.S. Application Serial No. 09/154,363, entitled Vertical Geometry InGaN LED

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Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449	U.S. Department of Commerce Patent and Trademark Office	Attorney Docket No. 5308-162	Serial No. 10/057,821
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)		Applicants: David B. Slater, Jr. et al.	
		Filing Date: 01/25/2002	GAU: 2815

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## U.S. PATENT DOCUMENTS

Examiner Initials	Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate
	1. 2003/0006418	01/09/03	Emerson et al.	257	79	
	2. 6,455,878	09/24/02	Bhat et al.	257	99	
	3. 6,187,606	02/13/01	Edmond et al.	438	46	
	4. 6,120,600	09/19/00	Edmond et al.	117	89	
	5. 5,739,554	04/14/98	Edmond et al.	257	103	
	6. 5,631,190	05/20/97	Negley	438	33	
	7. 5,604,135	02/18/97	Edmond et al.	437	22	
	8. 5,338,994	08/16/94	Lezan et al.	307	86	
	9. 5,027,168	06/25/91	Edmond	357	17	
	10. 4,918,497	04/17/90	Edmond	357	17	

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	11.	U.S. Application Serial No. 60,411,980, filed 09/19/02, <i>Phosphor-Coated Light Emitting Diodes Including Tapered Sidewalls, and Fabrication Methods</i>
	12.	U.S. Application Serial No. 10/003,331, filed 10/31/01, <i>Low Temperature Formation of Backside Ohmic Contacts for Vertical Devices</i>
	13.	U.S. Application Serial No. 60/294,445, filed May 30, 2001, <i>Multi-Quantum Well Light Emitting Diode Structure</i>
	14.	U.S. Application Serial No. 60/294,378, filed May 30, 2001, <i>Light Emitting Diode Structure With Multi-Quantum Well and Superlattice Structure</i>
	15.	U.S. Application Serial No. 60/294,308, filed May 30, 2001, <i>Light Emitting Diode Structure With Superlattice Structure</i>
	16.	U.S. Application Serial No. 09/787,189, filed 03/15/01, <i>Low Temperature Formation of Backside Ohmic Contacts for Vertical Devices</i>

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Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 5308-162		Serial No. 10/057,821	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Slater, Jr. et al.			
				Filing Date: January 25, 2002		GAU: 2812	
U.S. PATENT DOCUMENTS							
Examiner Initials		Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate
	1	5,779,924	01/18/00	Kish, Jr. et al.	438	29	
	2	5,779,924	07/14/98	Krames et al.	216	24	
	3	5,585,648	12/17/96	Tischler	257	77	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes / No
	4	61110476	05/28/86	Japan			X (Abstract)
	5	WO 00/33365	6/8/00	PCT			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	6	Invitation to Pay Additional Fees, Annex to Form PCT/ISA/206, Communication Relating to the Results of the Partial International Search, PCT/US02/02849, August 26, 2002					

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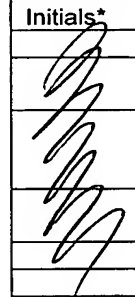
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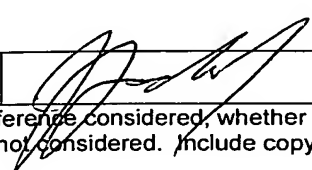
Substitute form 1449A/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		Application Number	10/057,821
		Filing Date	01/25/2002
		First Named Inventor	David B. Slater, Jr.
		Group Art Unit	2812
		Examiner Name	Savitri Mulpuri
Sheet 1 of 1	Attorney Docket Number	5308-162	

#### FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
		Office	Number	Kind Code (if known)				
	1	JP	11-191641		Matsushita Electron Corp.	07/13/1999		✓
	2	EP	0 051 172		Siemens Aktiengesellschaft	05/12/1982		

#### OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
	3	International Search Report, PCT/US02/02849, 12/02/2002	
	4	Mensz et al., <i>In<sub>x</sub>Ga<sub>1-x</sub>N/Al<sub>y</sub>Ga<sub>1-y</sub>N Violet Light Emitting Diodes With Reflective p-Contacts for High Single Sided Light Extraction</i> , Electronics Letters, Vol. 33, No. 24, November 20, 1997, pp. 2066-2068	
	5	Honma et al., <i>Evaluation of Barrier Metals of Solder Bumps for Flip-Chip Interconnection</i> , Electronic Manufacturing Technology Symposium, 1995, Proceedings of 1995 Japan International, 18 <sup>th</sup> IEEE/CPMT, December 4, 1995, pp. 113-116	
	6	Lee et al., <i>Bonding of InP Laser Diodes by Au-Sn Solder and Tungsten-Based Barrier Metallization Schemes</i> , Semiconductor Science and Technology, Vol. 9, No. 4, April 1994, pp. 379-386	

Examiner Signature		Date Considered	9/2
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